Vishay Siliconix

Low-Voltage, Low r_{ON}, Single Analog Switch In miniQFN-6 Package

DESCRIPTION

The DG2511/DG2512/DG2513 are low on-resistance, single-pole/double-throw or single-pole/single-throw monolithic CMOS analog switch. It is designed for low voltage applications. The DG2511/DG2512/DG2513 are ideal for portable and battery powered equipment, requiring high performance and efficient use of board space. In additional to the low onresistance (1.3 Ω at 2.7 V).

The DG2511 is an SPDT and the DG2512/DG2513 are SPST. The switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

The DG2511/DG2512/DG2513 are built on Vishay Siliconix's low voltage JI5L process. An epitaxial layer prevents latchup.

Break-before-make is guaranteed.

The DG2511/DG2512/DG2513 represents a breakthrough in packaging development for analog switching products. The miniQFN-6 package (1.2 x 1.0 mm).

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For analog switching products manufactured with NiPdAu device terminations, the lead (Pb)-free "-E4" suffix is being used as a designator.

FEATURES

- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance r_{ON}: 1.3 Ω at 2.7 V •
- Low Charge Injection
- Low Voltage Logic Compatible
- miniQFN-6 Package (1.2 x 1.0 mm)

BENEFITS

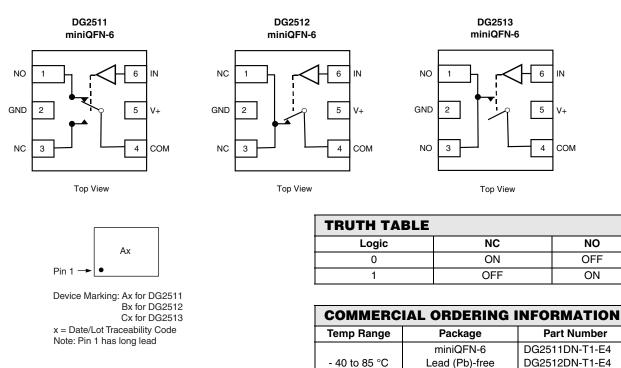
- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- **Reduce Board Space**
- Guaranteed 2 V Operation

APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- **Battery Operated Systems**
- Sample and Hold Circuits
- ADC and DAC Applications
- Low Voltage Data Acquisition Systems

with Tape and Reel

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





DG2513DN-T1-E4

NO

OFF

ON

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ABSOLUTE MAXIMUM RATINGS $T_A = 25 \,^{\circ}C$, unless otherwise noted

Parameter	Symbol	Limit	Unit			
Reference V+ to GND			- 0.3 to + 6			
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3 V)	v			
Continuous Current (NO, NC, COM pins)			± 150			
Peak Current (Pulsed at 1 ms, 10 % duty cycle)			± 300	mA		
Storage Temperature	D Suffix		- 65 to 150	°C		
Power Dissipation (Packages) ^b	miniQFN-6 ^c		160	mW		

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC Board.

c. Derate 2.0 mW/°C above 70 °C.

Parameter		Test Conditions		Limits			
		Otherwise Unless Specified			40 to 85 °		Unit
	Symbol	V+ = 3 V, \pm 10 %,V_{IN} = 0.4 V or 2.0 V e	Temp ^a	Min ^b	Тур ^с	Max ^b	
Analog Switch				-			
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}		Room Full		1.4	1.7 1.9	Ω
r _{ON} Match	Δr_{ON}	$V + = 2.7 V, V_{COM} = 0.5 V/1.5 V$	Room			0.15	
r _{ON} Flatness	r _{ON} Flatness	I _{NO} , I _{NC} = 100 mA	Room		0.3	0.4	
Switch Off Lookana Currant	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V, V _{NO} , V _{NC} = 1 V/3 V, V _{COM} = 3 V/1 V	Room Full	- 2 - 20		2 20	
Switch Off Leakage Current [†]	I _{COM(off)}		Room Full	- 2 - 20		2 20	nA
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 1 V/3 V	Room Full	- 2 - 20		2 20	
Digital Control				•	•	•	
Input High Voltage	V _{INH}		Full	1.6			v
Input Low Voltage	V _{INL}		Full			0.4	v
Input Capacitance	C _{in}		Full		4		pF
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ or } V+$	Full	1		1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}	V+ = 2.7 V, V _{NO} or V _{NC} = 1.5 V, R _L = 50 Ω , C _L = 35 pF	Room Full		18	43 49	
Turn-Off Time	t _{OFF}		Room Full		7	32 34	ns
Break-Before-Make Time	t _{BBM}		Room	1	12		
Charge Injection ^d	Q _{INJ}	${\sf C}_{\sf L}$ = 1 nF, ${\sf V}_{\sf GEN}$ = 0 V, ${\sf R}_{\sf GEN}$ = 0 Ω	Room		3		pC
Off-Isolation ^d	OIRR	R_L = 50 Ω , C_L = 5 pF, f = 1 MHz	Room		- 58		dB
Crosstalk ^d	X _{TALK}		Room		- 64		
N_{O} , N_{C} Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		21		pF
Channel-On Capacitance ^d	C _{ON}		Room		61		
Power Supply	•						
Power Supply Range	V+			1.8		5.5	V
Power Supply Current	I+	V _{IN} = 0 or V+			0.01	1.0	μA



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Parameter		Test Conditions Otherwise Unless Specified		Limits - 40 to 85 °C			
	Symbol	V+ = 5.0 V, \pm 10 %, V _{IN} = 0.6 V or 1.8 V ^e	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	v
On-Resistance	r _{ON}		Room Full		1	1.3 1.45	Ω
r _{ON} Match	Δr_{ON}	$V_{+} = 4.5 V, V_{COM} = 0.5 V/2.5 V,$	Room			0.15	
r _{ON} Flatness	r _{ON} Flatness	I _{NO} , I _{NC} = 100 mA	Room		0.3	0.4	
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}	V+ = 5.5 V, V _{NO} , V _{NC} = 1 V/4.5 V, V _{COM} = 4.5 V/1.0 V	Room Full	- 2 - 20		2 20	
Swith On Leakage Guneni	I _{COM(off)}		Room Full	- 2 - 20		2 20	nA
Channel-On Leakage Current	I _{COM(on)}	V+ = 5.5 V, V _{NO} , V _{NC} = V _{COM} = 1.0 V/4.5 V	Room Full	- 2 - 20		2 20	1
Digital Control							
Input High Voltage	V _{INH}		Full	1.8			v
Input Low Voltage	V _{INL}		Full			0.6	v
Input Capacitance	C _{in}		Full		4		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	1		1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}	$V_{\rm NO}$ or $V_{\rm NC}$ = 2.5 V, $\rm R_L$ = 50 Ω , $\rm C_L$ = 35 pF	Room Full		11	35 39	
Turn-Off Time	t _{OFF}		Room Full		6	31 33	ns
Break-Before-Make Time	t _{BBM}		Room	1	5		
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room		14		рС
Off-Isolation ^d	OIRR	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz	Room		- 58		dB
Crosstalk ^d	X _{TALK}		Room		- 64		
N _O , N _C Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		19		pF
Channel-On Capacitance ^d	C _{ON}		Room		61		
Power Supply							
Power Supply Range	V+	V _{IN} = 0 or V+		1.8		5.5	V
Power Supply Current	I+				0.01	1.0	μA

Notes:

a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, nor subjected to production test.

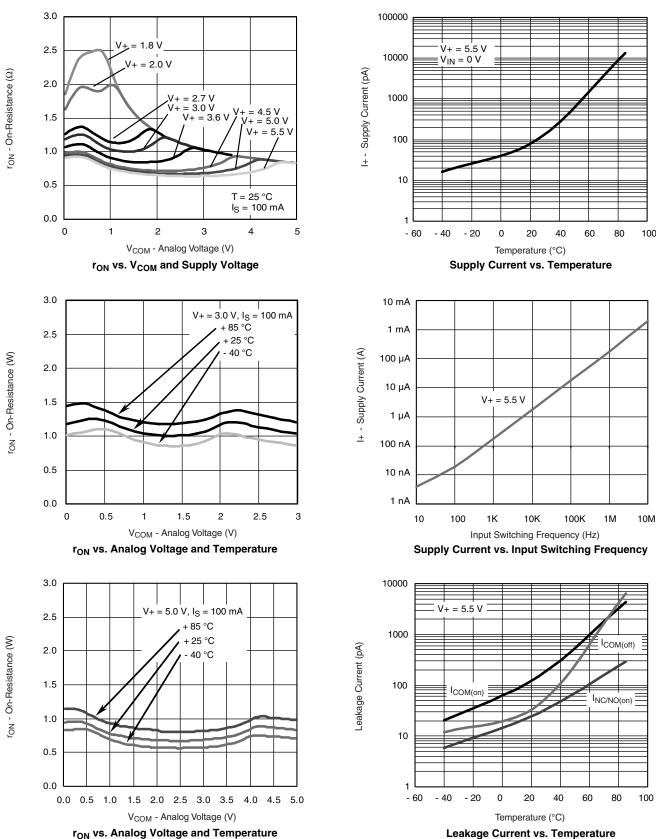
e. VIN = input voltage to perform proper function.

f. Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted



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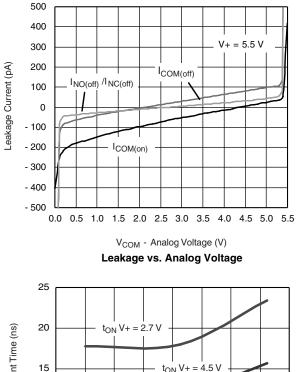
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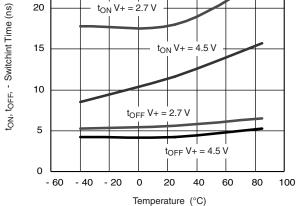
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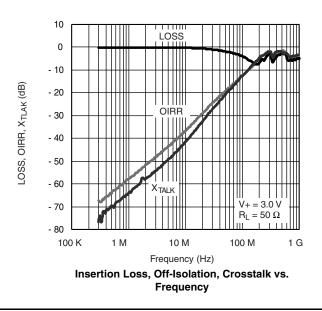
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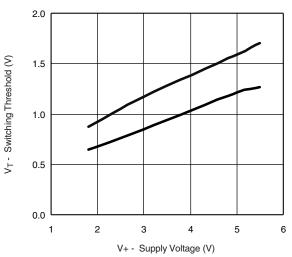




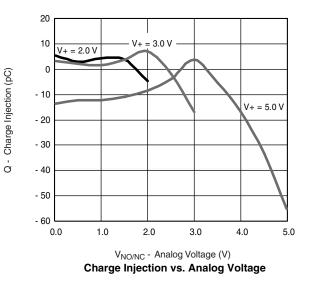


Switching Time vs. Temperature and Supply Voltage



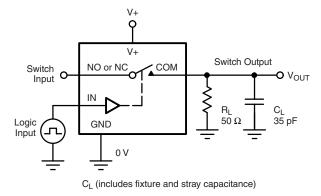


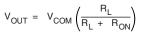
Switching Threshold vs. Supply Voltage

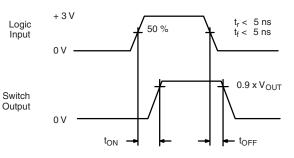


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TEST CIRCUITS







Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

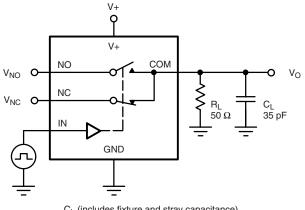
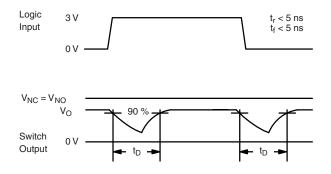
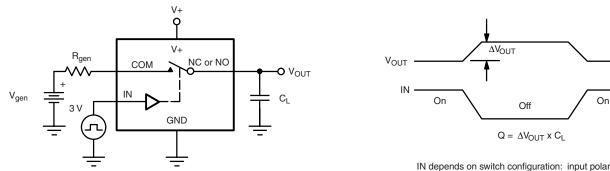


Figure 1. Switching Time



C_L (includes fixture and stray capacitance)

Figure 2. Break-Before-Make Interval



IN depends on switch configuration: input polarity determined by sense of switch.



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TEST CIRCUITS

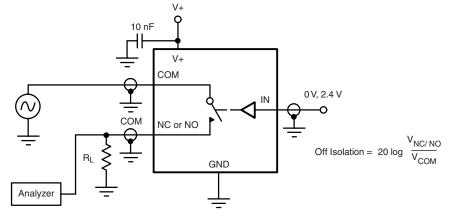


Figure 4. Off-Isolation

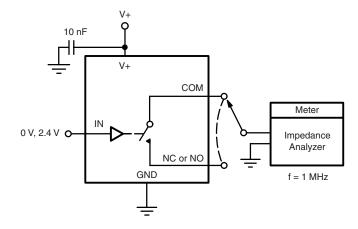


Figure 5. Channel Off/On Capacitance

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